



2N2327 thur 2N2329

SILICON THYRISTORS

All-diffused PNP thyristors designed for grating operation in mA/ μ A signal or detection circuits
 Compliance to RoHS.

MAXIMUM RATINGS (*)

$T_J=125^{\circ}\text{C}$ unless otherwise noted, $R_{GK}=1000\Omega$

Symbol	Ratings	2N2327	2N2328	2N2329	Unit
$V_{RSM(REP)}$	Peak reverse blocking voltage (1)	250	300	400	V
$V_{RSM(NON-REP)}$	Non-repetitive peak blocking reverse voltage ($t<5.0$ ms)	350	400	500	V
$I_{T(RMS)}$	Forward Current RMS (all conduction angles)	1.6			A
I_{TSM}	Peak Surge Current (One-Half Cycle, 60Hz) No Repetition Until Thermal Equilibrium is Restored.	15			A
P_{GM}	Peak Gate Power – Forward	0.1			W
$P_{G(AV)}$	Average Gate Power - Forward	0.01			W
I_{GM}	Peak Gate Current – Forward	0.1			A
V_{GFM}	Peak Gate Voltage - Forward	6.0			V
V_{GRM}	Peak Gate Voltage - Reverse	6.0			V
T_J	Operating Junction Temperature Range	-65 to +125			°C
T_{STG}	Storage Temperature Range	-65 to +150			

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ELECTRICAL CHARACTERISTICS (*)

T_J=25°C unless otherwise noted, R_{GK}=1000Ω

Symbol	Ratings	2N2327	2N2328	2N2329	Unit
V _{DRM}	Peak Forward Blocking Voltage (1) Min :	250	300	400	V
I _{RRM}	Peak Reverse Blocking Current (Rated V _{DRM} , T _J =125°C)	Max : 100			μA
I _{DRM}	Peak Forward Blocking Current (Rated V _{DRM} , T _J =125°C)	Max : 100			μA
V _T	Forward « on » Voltage I _T =1.0 A Peak	Max : 1.5			V
	I _T =1.0 A Peak T _C =85°C	Max : 2.0			
I _{GT}	Gate Trigger Current (2) Anode Voltage=6.0 Vdc, R _L =100Ω	Max : 200			μA
	Anode Voltage=6.0 Vdc, R _L =100Ω T _C =-65°C	Max : 350			
V _{GT}	Gate Trigger Voltage Anode Voltage=6.0 V, R _L =100Ω	Max : 0.8			V
	Anode Voltage=6.0 V, R _L =100Ω T _C =-65°C	Max : 1.0			
	V _{DRM} = Rated, R _L =100Ω T _J =125°C	Min : 0.1			
I _H	Holding Current Anode Voltage=6.0 V	Max : 2.0			mA
	Anode Voltage=6.0 V T _C =-65°C	Max : 3.0			
	Anode Voltage=6.0 V T _C =125°C	Min : 0.15			

(*) JEDEC Registered Values

(1) V_{RSM} and V_{DRM} can be applied for all types on a continuous dc basis without incurring damage.

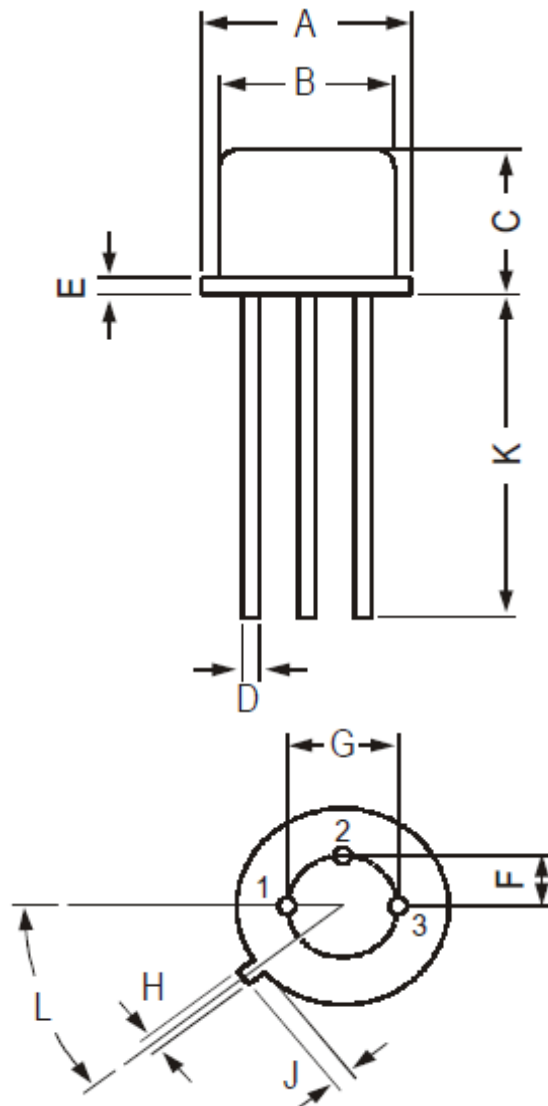
(2) R_{GK} current is not included in measurement.

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MECHANICAL DATA CASE TO-39

DIMENSIONS (mm)		
	min	max
A	8.50	9.39
B	7.74	8.50
C	6.09	6.60
D	0.40	0.53
E	-	0.88
F	2.41	2.66
G	4.82	5.33
H	0.71	0.86
J	0.73	1.02
K	12.70	-
L	42°	48°

Pin 1 :	kathode
Pin 2 :	Gate
Pin 3 :	Anode
Case :	anode



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